

### **isc Silicon NPN Power Transistors**

# **BUY77**

### DESCRIPTION

- Collector-Emitter Breakdown Voltage-: V<sub>(BR)CEO</sub> = 250V(Min.)
- Low Collector-Emitter Saturation Voltage-: V<sub>CE(sat)</sub>= 1.4V(Max.)@ I<sub>C</sub>= 5A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

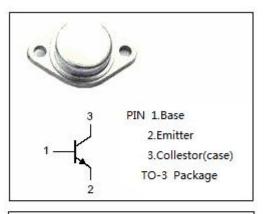
• Designed for use as high-speed power switches at high voltages.

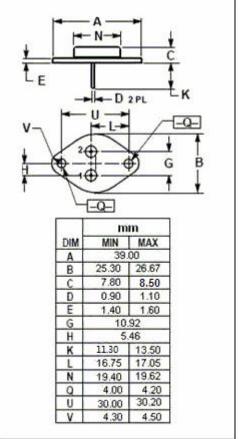
SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	400	V	
V <sub>CES</sub>	Collector-Emitter Voltage	400	V	
$V_{\text{CEO}}$	Collector-Emitter Voltage	250	V	
$V_{\text{EBO}}$	Emitter-Base Voltage	7	V	
lc	Collector Current-Continuous	8	А	
I <sub>CM</sub>	Collector Current-peak	10	A	
Pc	Collector Power Dissipation @Tc≤75℃			
Tj	Junction Temperature	175	°C	
T <sub>stg</sub>	Storage Temperature Range	-65~175	°C	

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.66	°C/W





isc website: www.iscsemi.com



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### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	250			v
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	400			v
$V_{(BR)CEV}$	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1mA; V <sub>BE</sub> = -3.5V	400			v
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	7			v
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1.25A			1.4	v
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1.25A			1.7	v
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 400V; I <sub>E</sub> = 0			1.0	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 1.5V	5			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V		15		MHz
t <sub>f</sub>	Fall Time	I <sub>C</sub> = 3A; I <sub>B1</sub> = -I <sub>B2</sub> = 0.6A			1.0	μ <b>S</b>

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